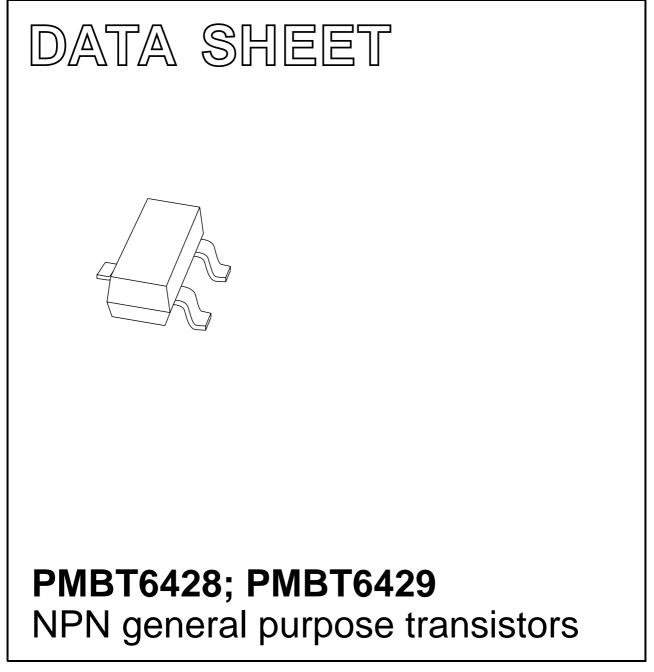
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 27 2004 Jan 22



FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 50 V).

APPLICATIONS

- General purpose switching and amplification
- Telephony and professional communication equipment.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT6428	*1K
PMBT6429	*1L

Note

- 1. * = p : Made in Hong Kong.
 - * = t : Made in Malaysia.

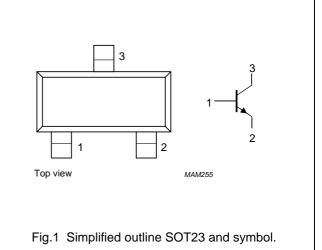
* = W : Made in China.

ORDERING INFORMATION

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	

PMBT6428; PMBT6429



TYPE	PACKAGE			
NUMBER	NAME DESCRIPTION		VERSION	
PMBT6428	_	plastic surface mounted package; 3 leads	SOT23	
PMBT6429				

PMBT6428; PMBT6429

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	PMBT6428		-	60	V
	PMBT6429		-	55	V
V _{CEO}	collector-emitter voltage	open base			
	PMBT6428		—	50	V
	PMBT6429		-	45	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current (DC)		—	100	mA
I _{CM}	peak collector current		—	200	mA
I _{BM}	peak base current		—	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	—	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

PMBT6428; PMBT6429

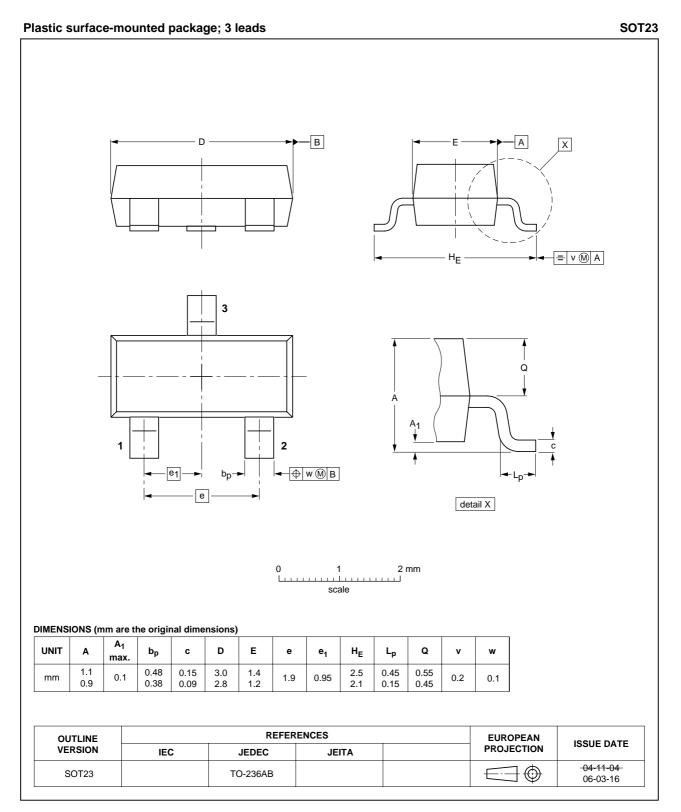
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	-	10	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	-	10	nA
h _{FE}	DC current gain	I _C = 0.1 mA; V _{CE} = 5 V			
	PMBT6428		250	650	
	PMBT6429		500	1250	
	DC current gain	I _C = 1 mA; V _{CE} = 5 V			
	PMBT6428		250	-	
	PMBT6429		500	_	
	DC current gain	I _C = 10 mA; V _{CE} = 5 V			
	PMBT6428		250	-	
	PMBT6429		500	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	200	mV
		I _C = 100 mA; I _B = 5 mA	-	600	mV
V _{BE}	base-emitter voltage	I _C = 1 mA; V _{CE} = 5 V	560	660	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	-	3	pF
C _e	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$	-	12	pF
f _T	transition frequency	$I_{C} = 1 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ f} = 100 \text{ MHz}$	100	700	MHz

PMBT6428; PMBT6429

PACKAGE OUTLINE



PMBT6428; PMBT6429

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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